# M. Sc. Electronics First Semester Analog Electronic Circuits & Devices (MSE-02)

Duration: 3Hrs.

Full Marks: 70

(PART-B: Descriptive)

Duration: 2 hrs. 40 mins.

Marks: 50

#### 1. Answer the following questions: (any five):

 $5 \times 2 = 10$ 

- a) Explain why an N-MOS is preferred than P-MOS?
- b) What are the limitations of h-parameters?
- c) Explain why CE configured transistor amplifier is preferred?
- d) Find -3dB frequency for an amplifier.
- e) Why voltage series feedback is commonly used in cascaded amplifier?
- f) What is the Barkhausen criterion for an Oscillator?
- g) Why an intrinsic semiconductor behaves like an insulator at absolute zero temperature?

#### 2. Answer the following questions: (any five)

 $5\times3=15$ 

- a) Explain the main differences between an ordinary diode and zener diode?
- b) Find an Expression of Fermi level in an intrinsic semiconductor.
- c) Find the relation between  $\alpha$  and  $\beta$ .
- d) For CE configured transistor prove that  $I_C = \beta I_B + (1+\beta)I_{CO}$

- e) For an n-channel JFET prove that  $g_m = g_{mo}(1-V_{GS}/Vp)$
- f) What are the characteristics of an ideal OP-AMP?
- g) Calculate  $V_{CE}$  for a CE transistor amplifier as shown in the Fig.1

Given:  $V_{CC} = 20V$   $V_{in} = 10V$   $V_{BE} = 0.7V$   $R_{C} = 3.3K\Omega$  $\beta = 200$ 

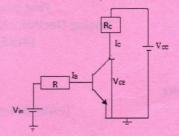


Fig.1

#### 3. Answer any five Questions : (any five)

5×5=25

- a) Find an expression of output voltage for an integrator by an OP-AMP.
- b) Show that the bandwidth increases in negative feedback amplifier.
- Find an expression for power efficiency of transformer coupled class a amplifier.
- d) Find an expression of pinch-off voltage for an n-channel JFET.
- e) Explain with neat diagram how CE npn transistor can be used as an amplifier as well as inverter.
- f) Explain the V-I characteristics curve of an n-channel MOSFET with different drain current.
- g) Find an expression for output voltage and calculate the output voltage for the given values as shown in the Fig.2

Given: R=1K,  $V_1=5V$ ,

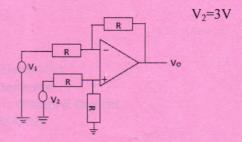


Fig.2

N.B: The symbols have usual meanings

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Time: 20 Min

Total marks: 20

# M.Sc. Electronics

## **First Semester**

## **ANALOG ELECTRONIC CIRCUITS & DEVICES**

(MSE - 02)

**PART A: Objective** 

	Sel	ect the correct answer: (All Qu	estions are compulsory): 20 >	< 1 = 20	
0	(put 'V' mark on the appropriate answer)				
	1.	. Which of the following transistor configuration produces 180° phase shift in output?			
		(a) CB	(b) CE		
		(c) CC	(d) All of them		
	2.	The cut-in voltage of a Germanium diode is			
		(a) 0.7V	(b) 0.2V		
		(c) 0.3V	(d) None		
	3.	The efficiency of a full wave rectifier is			
		(a) 46.6%	(b) 1.21		
		(c) 81.2%	(d) 0.21		
	4.	A negative feedback amplifie	er		
		(a) Increases gain	(b) Increases bandwidth		
		(c) Decreases bandwidth	(d) All of them		
	5.	If $V_{Smax}$ is the PIV of a half wave rectifier then the PIV of full wave rectifier is given by			
		(a) V <sub>Smax</sub>	(b) $\frac{VSmax}{a}$		
		(c) $2 V_{\text{Smax}}$	(d) $\sqrt{VSmax}$		
		(C) 2 V Smax	(u) VVSIIIaX		
	6.	In an intrinsic semiconductor the Fermi level lies			
		(a) Near conduction band	(b) Near valency band		
		(c) At middle band	(d) None		

At very high temperature an n-type semiconductor behaves like

(b) Metal

8. If  $\beta_1$  and  $\beta_2$  are the current gain of two transistor amplifier then overall current will be

(b)  $\beta_1 + \beta_2$ 

(d)  $\beta_1 \times \beta_2$ 

(d) Intrinsic semiconductor

(a) Insulator

(a)  $\frac{\beta 1}{\beta 2}$ 

(c)  $\beta_1 - \beta_2$ 

(c) p-type semiconductor

centre cut-off frequency will be	ff and upper cut –off frequency of an amplifier respectively then the
(a) $f_L \times f_H$	(b) $\frac{fL\times fH}{2}$
(c) $\frac{fL-fH}{2}$	(d) $\sqrt{fL \times fH}$
10. An ideal OP-AMP has	S ETHORICO DIMORTUSE BOJAKA
(a) Infinite bandwidth	(b) Infinite input impedance
(c) Infinite CMRR	(d) All of them.
(c) minimo emiliar	analytical A DAM
11. The audio frequency range is	
(a) 10Hz-20Hz	(b) 20Hz –20KHz
(c) 10MHz-20MHz	(d) 10KHz—20KHz
12 In FM radio the frequency range	in a (recollegation are equipment) (LA) convenie beares and the
12. In FM radio the frequency range (a) 87KHz—105KHz	(b) 87MHz—105MHz
(c) 90GHz—100GHz	(d) None
(c) 30GHZ -100GHZ	(d) None
13. If a differential amplifier has di	fferential mode gain 100 and common mode gain 0.01 then CMRR in
dB will be	
(a) 80dB	(b) 90dB
(c) 85dB	(d) 100dB
<sup>14.</sup> Which of the following is called	high speed logic family?
(a) TTL	(b) RTL
(c) DTL	(d) ECL
(c) BIL	(d) ECE
15. As temperature increases the m	obility of carriers in semiconductor
(a) Increases	(b) Decreases
(c) Remains constant	(d) None
16. In FETs the carriers move by the	ne process of
(a) Diffusion only	(b) Drift only
(c) Diffusion and Drift	(d) None
17 16 4 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
(a) 100	0.99 then the current gain in CC transistor amplifier will be (b) 101
(c) 0.99	(d) 99
(c) 0.99	(d) 33
18. In BJT the current flows due to	
(a) Electrons only	(b) Holes only
(c) Both electrons and holes	
19. In an n-channel FET current flo	
(a) Electrons only	(b) Holes only
(c) Both electrons and holes	d) none
20. In an npn transistor the buried l	aver on the n-type substrate is
(a) n <sup>+</sup> doped	(b) p <sup>+</sup> doped
(c) both n <sup>+</sup> and p <sup>+</sup> doped	(d) none
(e) com in and p doped	(d) none

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